

# 2SC5592

### Silicon NPN epitaxial planar type

For DC-DC converter
For various driver circuits

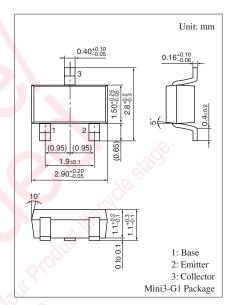
#### ■ Features

- Low collector-emitter saturation voltage V<sub>CE(sat)</sub>
- High-speed switching
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing

#### ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	$V_{CBO}$	15	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	15	V	
Emitter-base voltage (Collector open)	$V_{EBO}$	5	V	
Collector current	$I_{C}$	2.5	A	
Peak collector current	$I_{CP}$	10	A	
Collector power dissipation *	P <sub>C</sub>	600	mW	
Junction temperature	Tj	150	°C	
Storage temperature	$T_{stg}$	-55 to +150	°C	

Note) \*: Measure on the ceramic substrate at  $15 \text{ mm} \times 15 \text{ mm} \times 0.6 \text{ mm}$ 



Marking Symbol: 2T

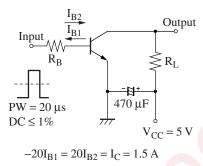
### ■ Electrical Characteristics $T_a = 25$ °C $\pm 3$ °C

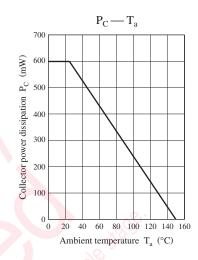
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_C = 10 \mu\text{A},  I_E = 0$	15	55		V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_C = 1 \text{ mA}, I_B = 0$	15			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = 10  \mu A, I_C = 0$	5			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 10 \text{ V}, I_{E} = 0$			0.1	μΑ
Forward current transfer ratio *	h <sub>FE1</sub>	$V_{CE} = 2 \text{ V}, I_{C} = 100 \text{ mA}$	400		1000	_
	h <sub>FE2</sub>	$V_{CE} = 2 \text{ V}, I_{C} = 2.5 \text{ A}$	280			
Collector-emitter saturation voltage *	V <sub>CE(sat)</sub>	$I_C = 1 \text{ A}, I_B = 10 \text{ mA}$		110		mV
		$I_C = 2.5 \text{ A}, I_B = 50 \text{ mA}$		220	320	
Transition frequency	$f_T$	$V_{CB} = 10 \text{ V}, I_E = -50 \text{ mA}, f = 200 \text{ MHz}$		180		MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		30		pF
(Common base, input open circuited)						
Turn-on time	t <sub>on</sub>	Refer to the switching time measurement circuit		30		ns
Storage time	t <sub>stg</sub>			100		ns
Fall time	t <sub>f</sub>			10		ns

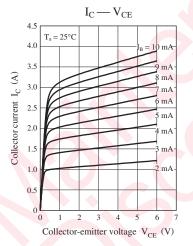
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

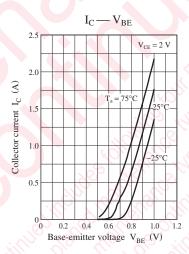
2. \*: Pulse measurement (≤ 1 ms)

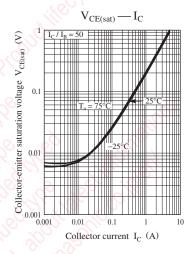
Switching time measurement circuit

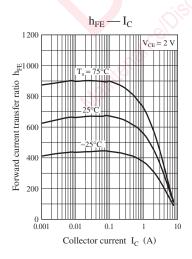


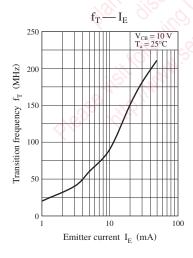


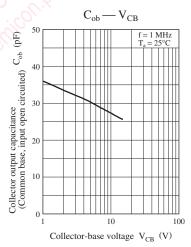












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